



D. Marchi
6-5-03
Amend B

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q65032

Dinesh Kumar SOOD, et al.

Appln. No.: 09/883,220

Group Art Unit: 2832

Confirmation No.: 9834

Examiner: Bernard ROJAS

Filed: June 19, 2001

For: BI-STABLE MICROSWITCH INCLUDING MAGNETIC LATCH

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated February 27, 2003, please amend the above-identified application as follows:

IN THE SPECIFICATION:

At page 4, replace the first full paragraph with the following new paragraph:

BI

An insulating dielectric layer 6 is then formed on the other surface of the substrate 2. The dielectric layer 6 may be formed from SiO₂, SiN₂, polyamide or like material. A layer 7 of thermalloy or other magnetisable material is then electro formed on the dielectric layer 6. The composition of the thermalloy layer 7 is adjusted to set the Curie temperature of the layer. A further dielectric layer may then be formed on the thermalloy layer 7, and electrical contacts a" and b" formed on the surface of that dielectric layer. An electrical resistance element 8, such as

RECEIVED
MAY 29 2003
TECHNOLOGY CENTER 2800